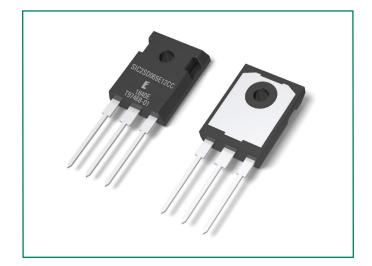
# LSIC2SD065E12CCA 650 V, 12 A SiC Schottky Barrier Diode









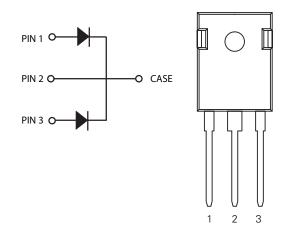
#### **Description**

This series of silicon carbide (SiC) Schottky diodes has negligible reverse recovery current, high surge capability, and a maximum operating junction temperature of 175 °C. This diode series is ideal for applications where improvements in efficiency, reliability, and thermal management are desired.

#### **Features**

- AEC-Q101 qualified
- Positive temperature coefficient for safe operation and ease of paralleling
- 175 °C. maximum operating junction temperature
- · Excellent surge capability
- Extremely fast, temperature-independent switching behavior
- Dramatically reduced switching losses compared to Si bipolar diodes

#### Circuit Diagram TO-247-3L



#### **Applications**

- · Boost diodes in PFC or DC/DC stages
- Switch-mode power supplies
- Uninterruptible power supplies
- Solar inverters
- Industrial motor drives
- EV charging stations

#### **Environmental**

- Littelfuse "RoHS" logo = RoHS RoHS conform
- Littelfuse "HF" logo = HF Halogen Free
- Littelfuse "Pb-free" logo = Pb Pb-free lead plating



## **Maximum Ratings**

Characteristics	Symbol	Conditions	Value	Unit	
Repetitive Peak Reverse Voltage	V <sub>RRM</sub>	-	650	V	
DC Blocking Voltage	V <sub>R</sub>	T <sub>J</sub> = 25 °C	650	V	
Continuous Forward Current (Per Leg/Component)	I <sub>F</sub>	T <sub>C</sub> = 25 °C	18.5 / 37	А	
		T <sub>C</sub> = 152 °C	6 / 12		
Non-Repetitive Forward Surge Current (Per Leg)	I <sub>FSM</sub>	$T_{\rm C}$ = 25 °C, $t_{\rm P}$ = 10 ms, Half sine pulse	32	А	
Power Dissipation (Per Leg/Component)	P <sub>Tot</sub>	T <sub>c</sub> = 25 °C	75 / 150	W	
		T <sub>C</sub> = 110 °C	32 / 64		
Operating Junction Temperature	T <sub>J</sub>	-	-55 to 175	°C	
Storage Temperature	T <sub>STG</sub>	-	-55 to 150	°C	
Soldering Temperature	T <sub>sold</sub>	-	260	°C	

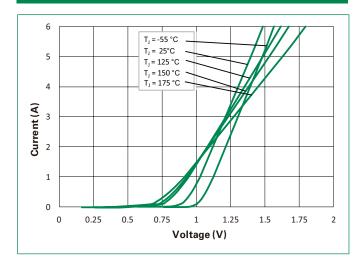
## Electrical Characteristics (T<sub>1</sub> = 25 °C unless otherwise specified)

Characteristics Syr			Value				
	Symbol	Conditions	Min.	Тур.	Max.	Unit	
Forward Voltage	V <sub>F</sub>	I <sub>F</sub> = 6 A, T <sub>J</sub> = 25 °C	-	1.5	1.8	V	
		I <sub>F</sub> = 6 A, T <sub>J</sub> = 175 °C	-	1.85	-	V	
Reverse Current	I <sub>R</sub>	$V_{_{\rm R}}=650{\rm V},T_{_{\rm J}}=25{\rm ^{\circ}C}$	-	<1	50	μA	
		$V_{_{\rm R}} = 650  \text{V, T}_{_{\rm J}} = 175  ^{\circ}\text{C}$	-	15	-	μΑ	
Total Capacitance	С	$V_R = 1 V, f = 1 MHz$	-	300	-		
		$V_R = 200  \text{V},  \text{f} = 1  \text{MHz}$	-	39	-	pF	
		$V_R = 400  \text{V},  \text{f} = 1  \text{MHz}$	-	28	-		
Total Capacitive Charge	Q <sub>c</sub>	$V_{R} = 400 \text{ V},  Q_{C} = \int_{0}^{V_{R}} C(V) dV$	-	20	-	nC	

## **Thermal Characteristics**

Characteristics	Symbol	Value	Unit
Thermal Resistance (Per Leg/Component)	R	2 / 1	°C/W

## Figure 1: Typical Foward Characteristics



## **Figure 2: Typical Reverse Characteristics**

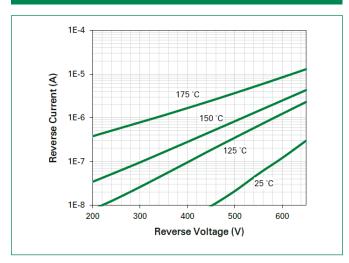




Figure 3: Power Derating

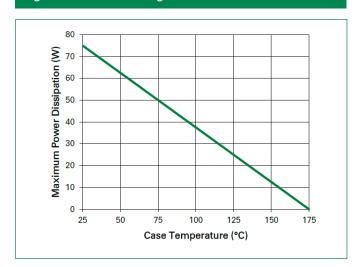


Figure 4: Current Derating

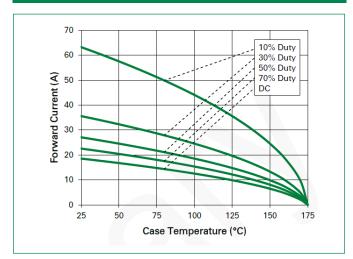


Figure 5: Capacitance vs. Reverse Voltage

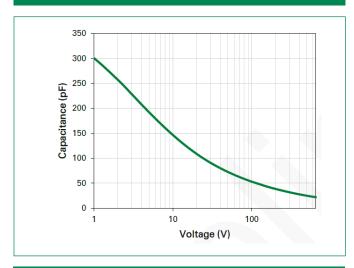


Figure 6: Capacitive Charge vs. Reverse Voltage

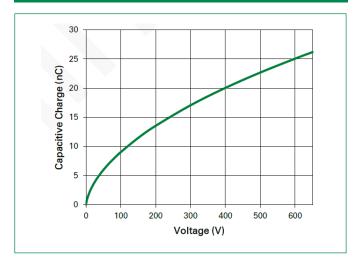


Figure 7: Stored Energy vs. Reverse Voltage

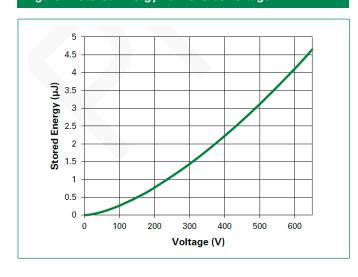
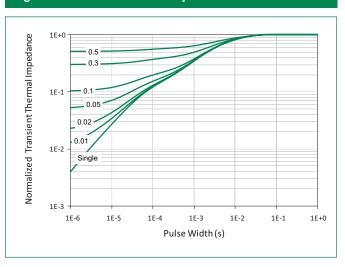
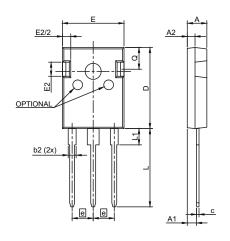


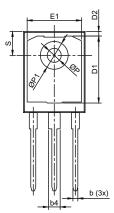
Figure 8: Transient Thermal Impedance



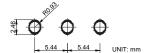
# GEN2 SiC Schottky Diode LSIC2SD065E12CCA, 650 V, 12 A, TO-247-3L

## Package Dimensions TO-247-3L





#### Recommended Hole Pattern Layout

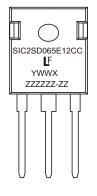


#### Notes:

- Dimensions are in millimeters
- Dimension D, E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These measured at the outermost extreme of plastic body. 3.øP to have a maximum draft angle of 1.5° to the top
- of the part with a maximum hole diameter of 0.154"

Cumbal	Millimeters				
Symbol	Min	Nom	Max		
А	4.80	5.03	5.20		
A1	2.25	2.38	2.54		
A2	1.85	1.98	2.11		
b	0.99	-	1.40		
b2	1.65	-	2.39		
b4	2.59	-	3.43		
С	0.38	0.64	0.89		
D	20.80	20.96	21.34		
D1	13.50	-	-		
D2	0.51	1.19	1.35		
е	5.44 BSC				
Е	15.75	15.90	16.13		
E1	13.06	14.02	14.15		
E2	4.19	4.32	4.83		
L	19.81	20.19	20.57		
L1	3.81	4.19	4.45		
øΡ	3.55	3.61	3.66		
øP1	7.06	7.19	7.32		
Q	5.49	5.61	6.20		
S	6.05	6.17	6.30		

## **Part Numbering and Marking System**



SIC = SiC 2 = Gen2

SD = Schottky Diode 065 = Voltage Rating (650 V)

= TO-247-3L Ε

12 = Current Rating (12 A)

CC = Common Cathode = Year

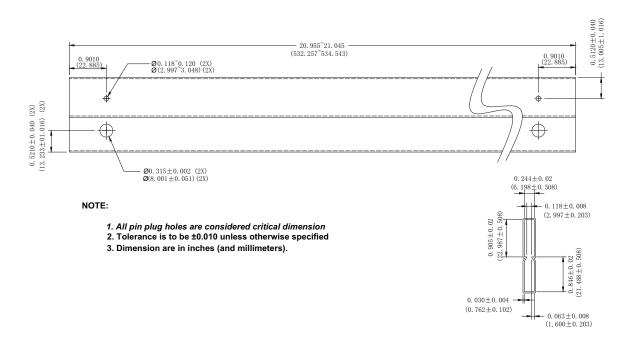
WW = Week = Special Code Χ ZZZZZZ-ZZ = Lot Number

## **Packing Options**

Part Number	Marking	Packing Mode	M.O.Q
LSIC2SD065E12CCA	SIC2SD065E12CC	Tube (30pcs)	450

## GEN2 SiC Schottky Diode LSIC2SD065E12CCA, 650 V, 12 A, TO-247-3L

#### **Packing Specification TO-247-3L**



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